

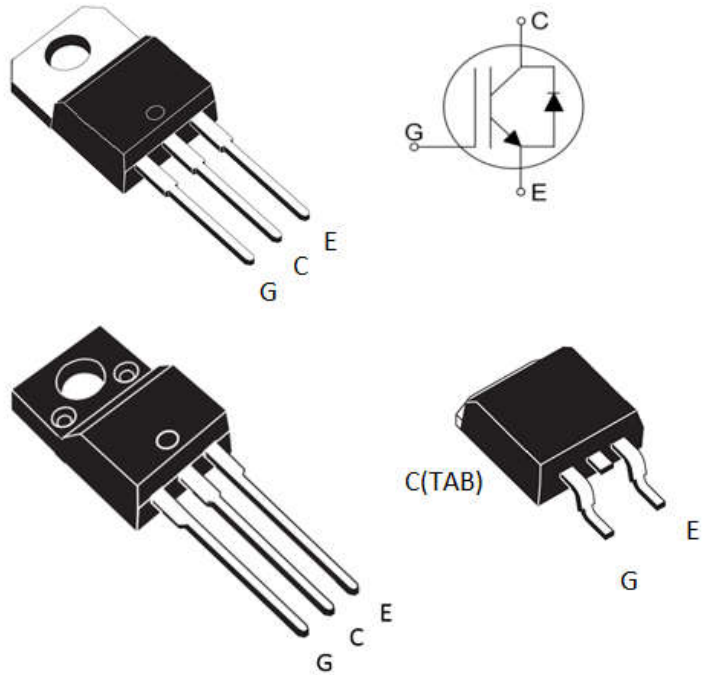
Features

- Max Junction Temperature 150°C
- High breakdown voltage up to 650V for improved reliability
- Short Circuit Rated
- Very Low Saturation Voltage:
 $V_{CE(SAT)} = 1.9V$ (Typ.) @ $I_C = 20A$
- Soft current turn-off waveforms

V_{CE}	650	V
I_C	20	A
$V_{CE(SAT)} \quad I_C=20A$	1.90	V

Applications

- Soft switching applications
- Air conditioning
- Motor drive inverter



Product	Package	Packaging
HMG20N65	TO-220	Tube
HMG20N65D	TO-263	Tube
HMG20N65F	TO-220F	Tube

Maximum Ratings ($T_j = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Value	Unit
Collector-Emitter Breakdown Voltage	V_{CE}	650	V
DC collector current, limited by T_{jmax} $T_C = 25^\circ\text{C}$ $T_C = 100^\circ\text{C}$	I_C	40 20	A
Diode Forward current, limited by T_{jmax} $T_C = 25^\circ\text{C}$ $T_C = 100^\circ\text{C}$	I_F	40 20	A
Continuous Gate-emitter voltage	V_{GE}	± 20	V
Transient Gate-emitter voltage	V_{GE}	± 30	V
Turn off safe operating area $V_{CE} \leq 650\text{V}$, $T_j \leq 150^\circ\text{C}$	-	80	A
Pulsed collector current, $V_{GE}=15\text{V}$, t_p limited by T_{jmax}	I_{CM}	80	A
Short Circuit Withstand Time, $V_{GE}=15\text{V}$, $V_{CE} \leq 400\text{V}$	T_{sc}	5	μs
TO-220F Power dissipation, $T_j=25^\circ\text{C}$	P_{tot}	27	W
TO-220, TO-263, Power dissipation, $T_j=25^\circ\text{C}$	P_{tot}	105	W
Operating junction temperature	T_j	$-40 \dots +150$	$^\circ\text{C}$
Storage temperature	T_s	$-55 \dots +150$	$^\circ\text{C}$
Soldering temperature, wave soldering 1.6mm (0.063in.) from case for 10s	-	260	$^\circ\text{C}$

Thermal Resistance

Parameter	Symbol	TO-220, TO-263	TO-220F	Unit
IGBT thermal resistance, junction - case	$R_{\theta(j-c)}$	1.2	4.9	K/W
Diode thermal resistance, junction - case	$R_{\theta(j-c)}$	2.38	5.8	K/W
Thermal resistance, junction - ambient	$R_{\theta(j-a)}$	62.5		K/W

Electrical Characteristics of the IGBT (T_J= 25°C unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
Static Characteristics (Tested on wafers)						
BV _{CES}	Collector to Emitter Breakdown Voltage	V _{GE} = 0V, I _C = 1mA	650	-	-	V
V _{CE(SAT)}	Collector to Emitter Saturation Voltage	I _C = 20A, V _{GE} = 15V	-	1.9	2.2	V
V _{GE(th)}	G-E Threshold Voltage	V _{GE} = V _{CE} , I _C = 250μA	4.1	5.0	5.7	V
I _{CES}	Collector Cut-Off Current	V _{CE} = 650V, V _{GE} = 0V	-	-	25	μA
I _{GES}	G-E Leakage Current	V _{GE} = ±20V, V _{CE} = 0V	-	-	±200	nA
g _{fs}	Transconductance	V _{CE} =20V, I _C =15A	-	10	-	S

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Dynamic						
Input capacitance	C _{ies}	V _{CE} = 25V, V _{GE} = 0V, f = 1MHz	-	990	-	pF
Output capacitance	C _{oes}		-	56	-	
Reverse transfer capacitance	C _{res}		-	30	-	
Gate charge	Q _G	V _{CC} = 480V, I _C = 20A, V _{GE} = 15V	-	52	-	nC
Short circuit collector current	I _{C (SC)}	V _{GE} =15V, t _{SC} ≤ 5us V _{CC} =400V, T _{j, start} =25°C	-	98	-	A

Switching Characteristic, Inductive Load (T_j= 25°C unless otherwise specified)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Dynamic						
Turn-on Delay Time	t _{d(on)}	T _j =25°C V _{CC} = 400V, I _C = 20A, V _{GE} = 0/15V, R _g =12Ω	-	13	-	ns
Rise Time	t _r		-	20	-	ns
Turn-off Delay Time	t _{d(off)}		-	60	-	ns
Fall Time	t _f		-	40	-	ns
Turn-on Energy	E _{on}		-	1.0	-	mJ
Turn-off Energy	E _{off}		-	0.2	-	mJ

Electrical Characteristics of the DIODE (T_j= 25°C unless otherwise specified)

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Dynamic						
Diode Forward Voltage	V _{FM}	I _F = 20A	-	1.9	-	V
Reverse Recovery Time	T _{rr}	I _F = 15A VR = 300V, di/dt =200A/μs	-	50	-	ns
Reverse Recovery Current	I _{rr}		-	4	-	A
Reverse Recovery Charge	Q _{rr}		-	83	-	nC

Fig. 1 FBSOA characteristics for TO-220F

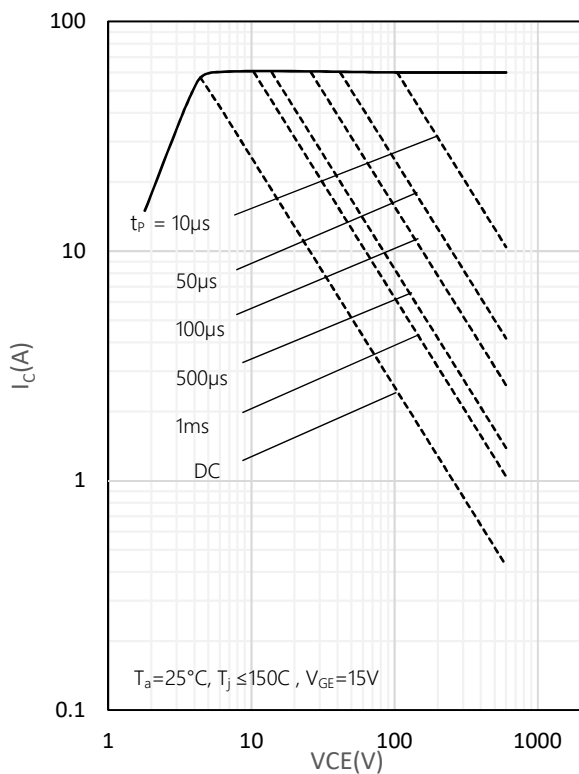


Fig. 2 FBSOA characteristics for TO-220 and TO-263

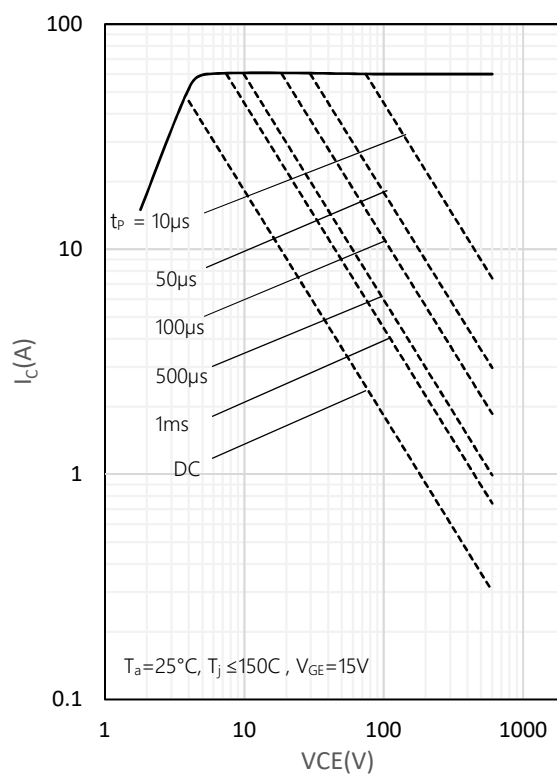


Fig. 3 Load Current vs. Frequency for TO-220F

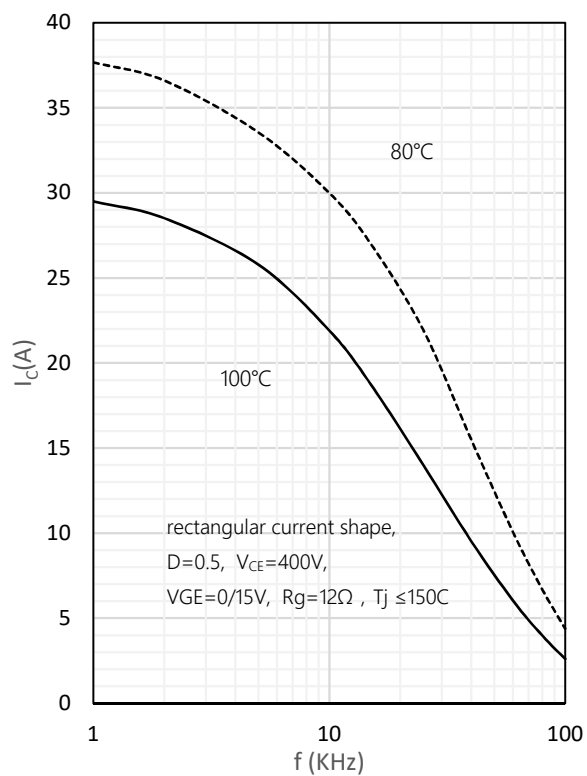


Fig.4 Load Current vs. Frequency TO-220 and TO-263

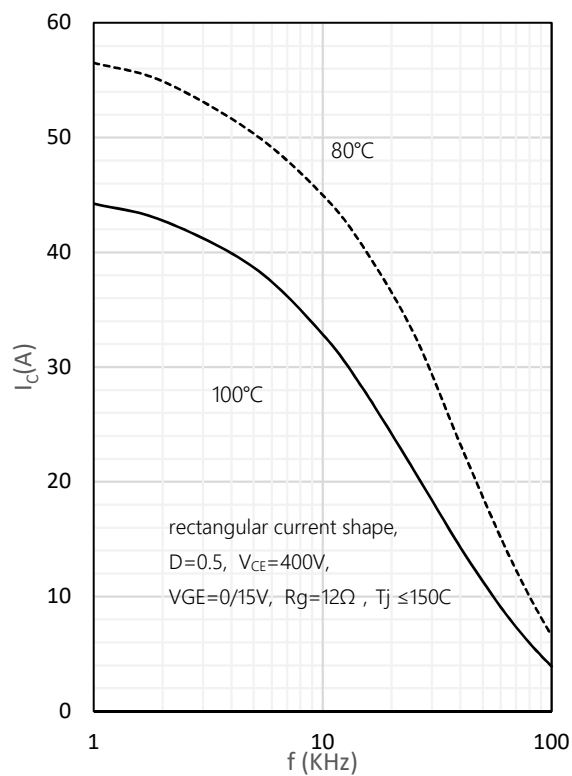


Fig. 5 Output characteristics

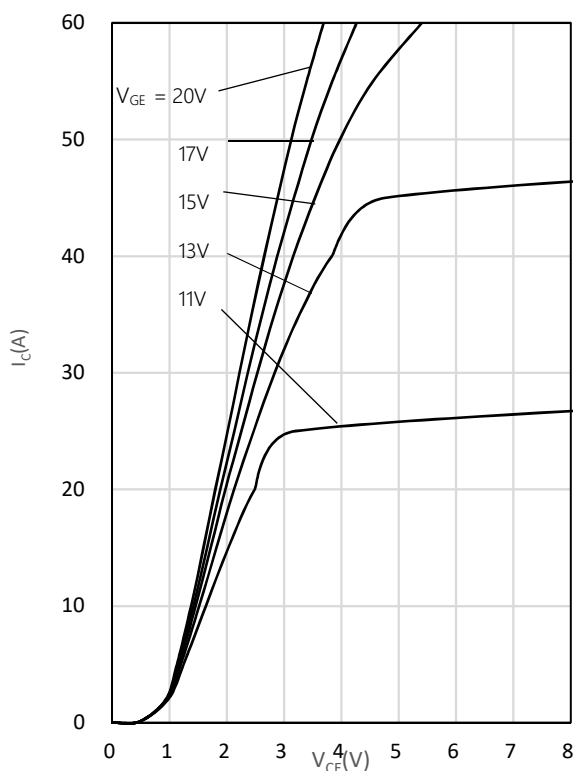


Fig. 6 Saturation voltage characteristics

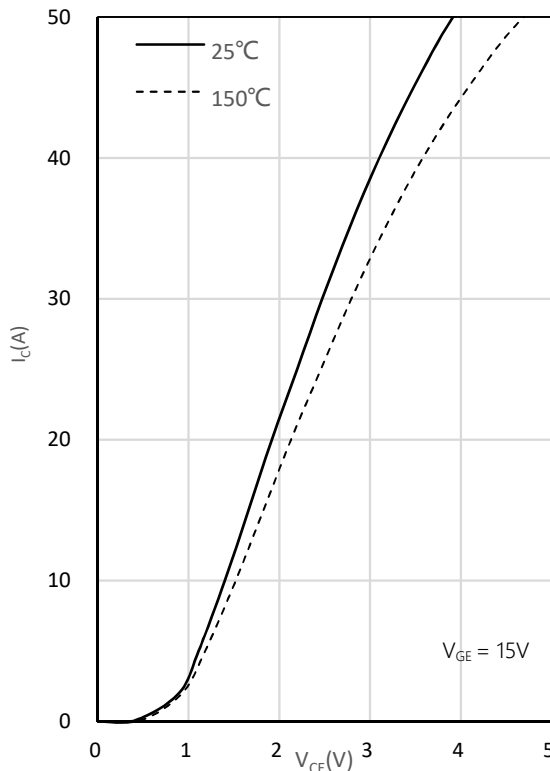


Fig. 7 Switching times vs. gate resistor

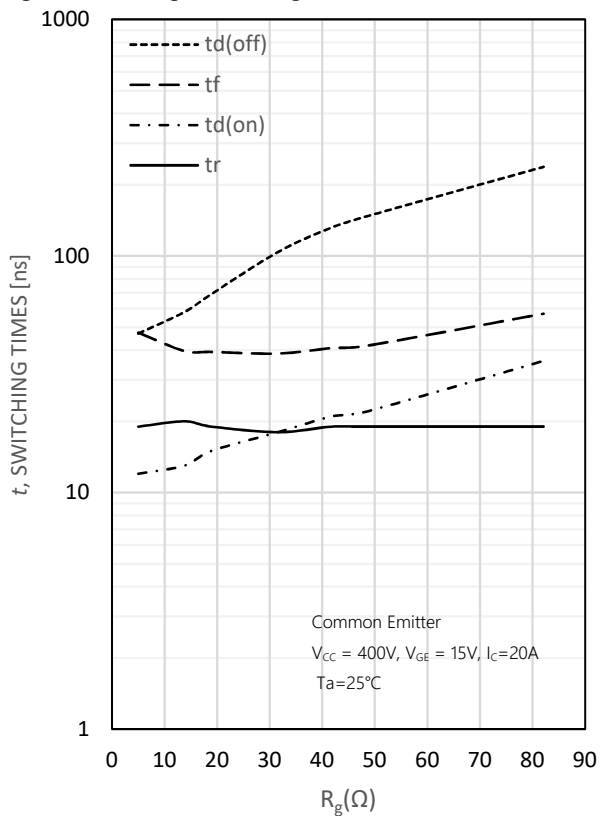


Fig. 8 Switching times vs. collector current

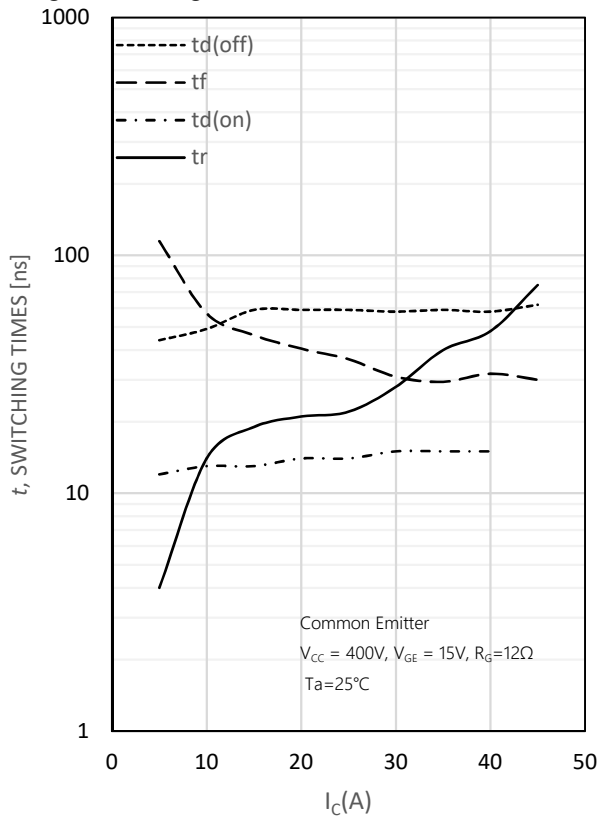


Fig. 9 Switching loss vs. gate resistor

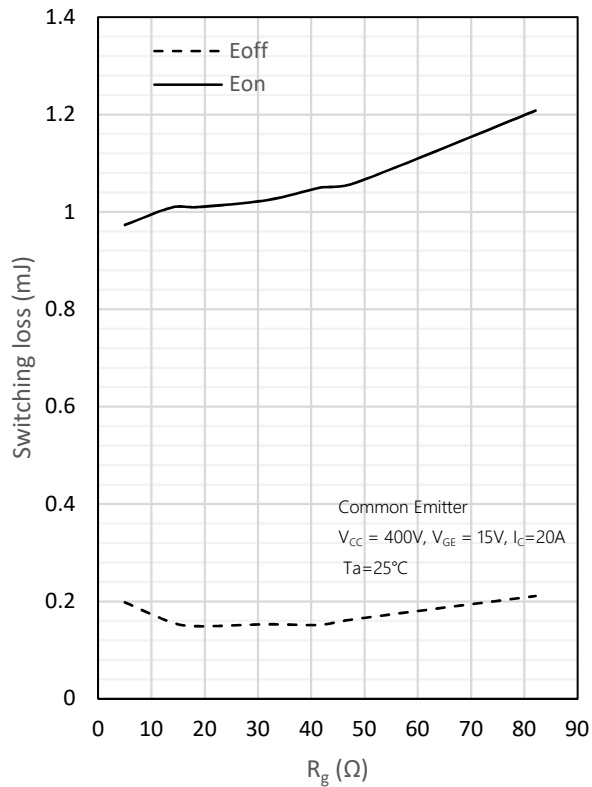


Fig. 10 Switching loss vs. collector current

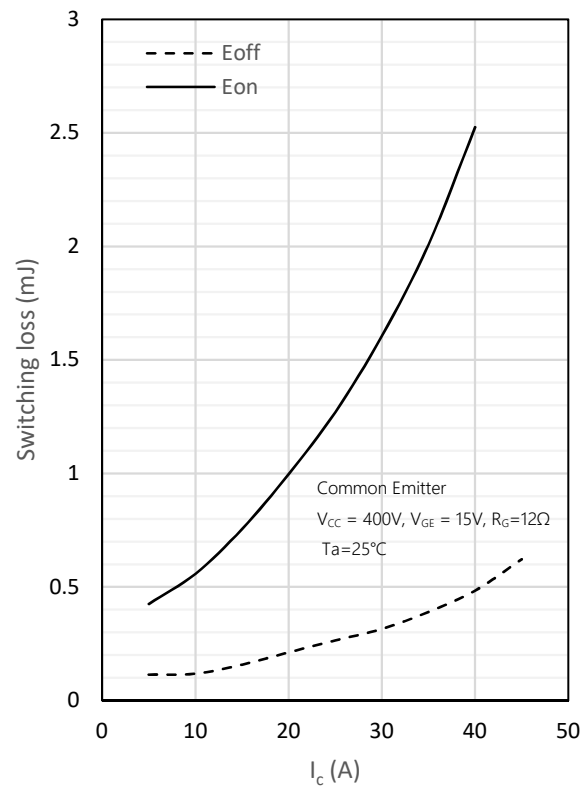


Fig. 11 Gate charge characteristics

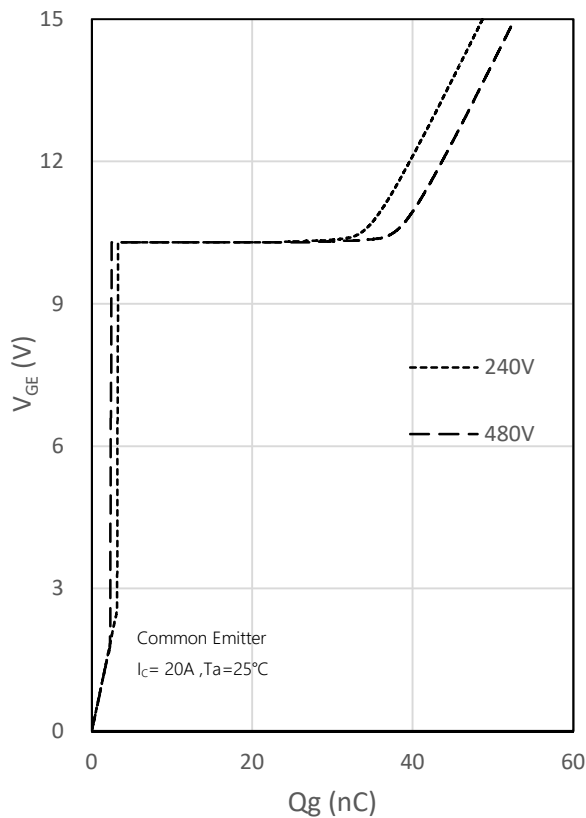
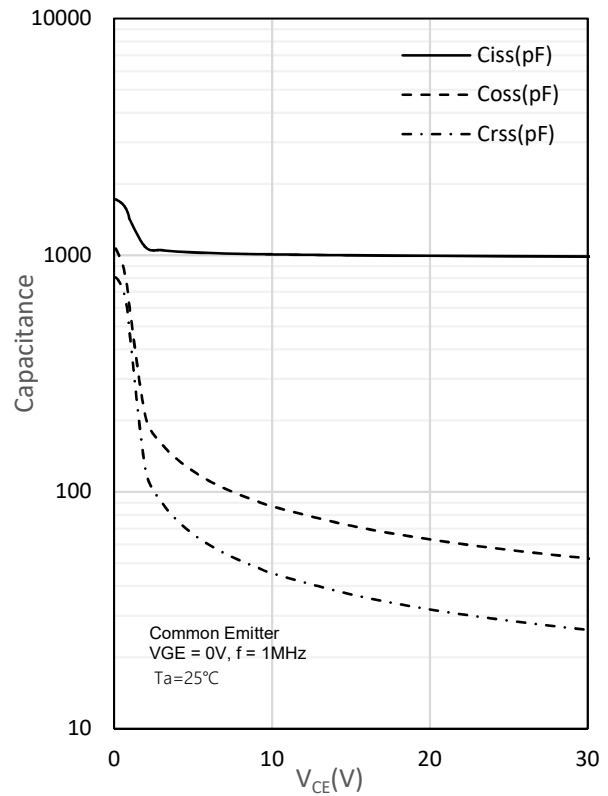
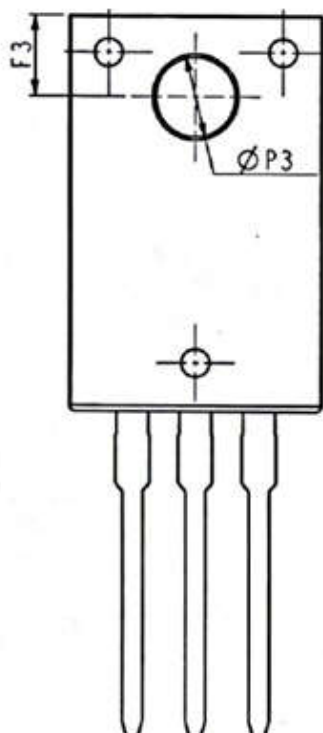
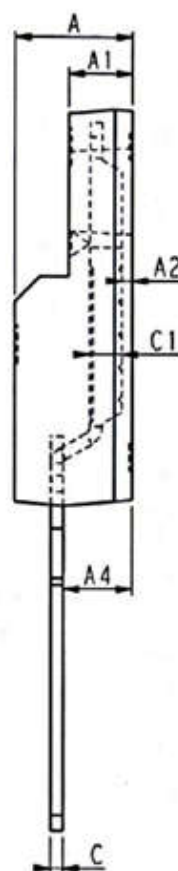
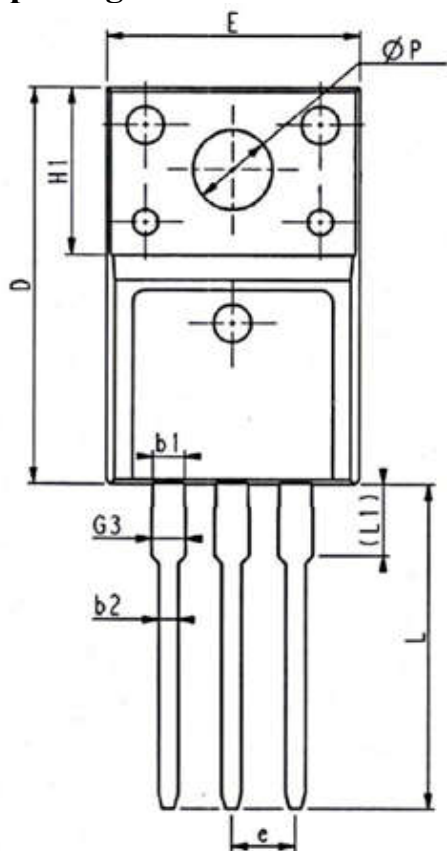


Fig. 12 Capacitance characteristics

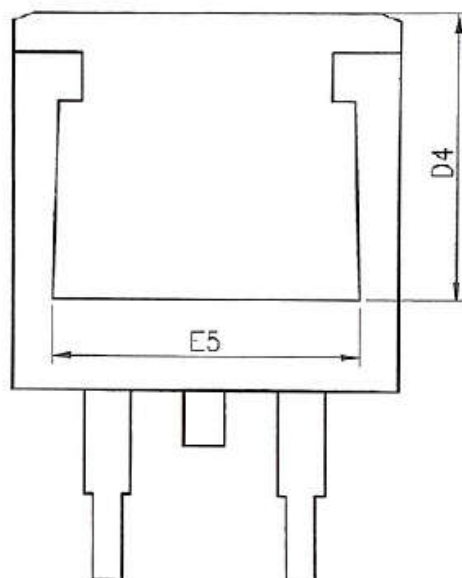
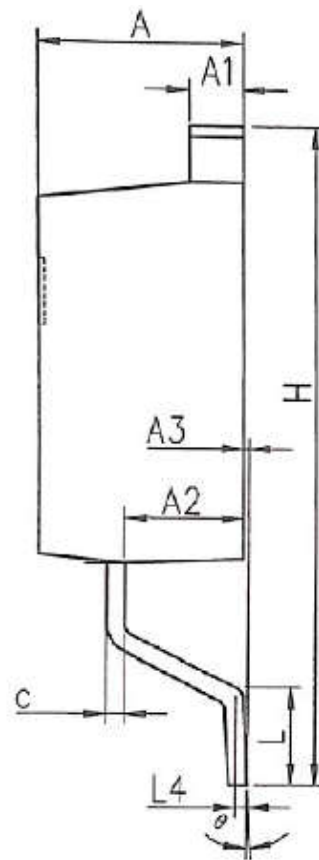
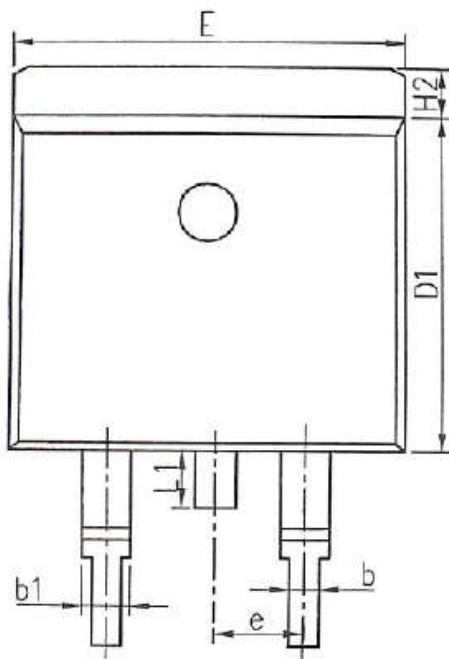


TO-220F package information



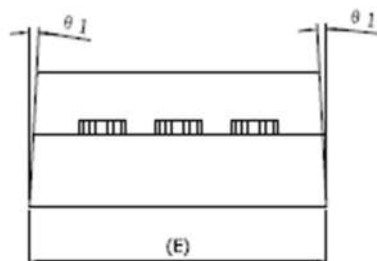
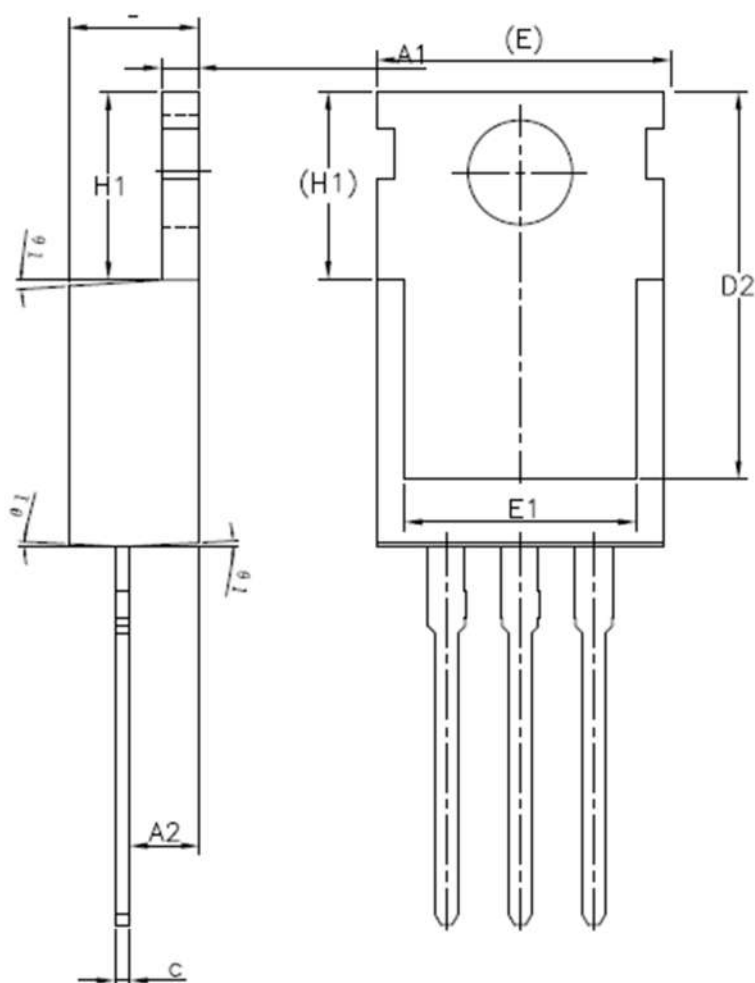
SYMBOL	MIN	NOM	MAX
E	9.96	10.16	10.36
A	4.50	4.70	4.90
A1	2.34	2.54	2.74
A2	0.30	0.45	0.60
A4	2.56	2.76	2.96
c	0.40	0.50	0.65
c1	1.20	1.30	1.35
D	15.57	15.87	16.17
H1	6.70REF		
e	2.54BSC		
L	12.68	12.98	13.28
L1	2.88	3.03	3.18
ØP	3.03	3.18	3.38
ØP3	3.15	3.45	3.65
F3	3.15	3.30	3.45
G3	1.25	1.35	1.55
b1	1.18	1.28	1.43
b2	0.70	0.80	0.95

TO-263 package information



SYMBOL	MM		
	MIN	NOM	MAX
A	4.37	4.57	4.77
A1	1.22	1.27	1.42
A2	2.49	2.69	2.89
A3	0.00	0.13	0.25
b	0.70	0.81	0.96
b1	1.17	1.27	1.47
c	0.30	0.38	0.53
D1	8.50	8.70	8.90
D4	6.60	-	-
E	9.88	10.16	10.36
E5	7.06	-	-
e	2.54 BSC		
H	14.70	15.10	15.50
H2	1.07	1.27	1.47
L	2.00	2.30	2.60
L1	1.40	1.55	1.70
L4	0.25 BSC		
θ	0°	5°	9°

TO-220 package information



SYMBOL	MIN	NOM	MAX
A	4.40	4.50	4.60
A1	1.27	1.30	1.33
A2	2.30	2.40	2.50
b	0.70	—	0.90
b1	1.27	—	1.40
c	0.45	0.50	0.60
D	15.30	15.70	16.10
D1	9.10	9.20	9.30
D2	13.10	—	13.70
E	9.70	9.90	10.20
E1	7.80	8.00	8.20
e	2.54BSC		
e1	5.08BSC		
H1	6.30	6.50	6.70
L	12.78	13.08	13.38
L1	—	—	3.50
L2	4.60REF		
ϕP	3.55	3.60	3.65
Q	2.73	—	2.87
θ_1	1°	3°	5°

